

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	0	gan and p-electrode and ag and antireflection	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/02/27 12:57
2	BRS	L2	9	gan and p-electrode and ag	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/02/27 12:51
3	BRS	L3	472	gan and ag	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/02/27 12:51
4	BRS	L4	5	3 and nakamura.in.	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/02/27 12:53
5	BRS	L5	5	4 and ag	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/02/27 12:53
6	BRS	L6	0	gan and (p-side p-contact) and ag and antireflection	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/02/27 12:57

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L7	34	gan and (p-side p-contact) and ag	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/02/27 13:45
8	BRS	L8	260	(light adj emitting adj diode) and antireflection	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/02/27 13:46